



#### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

## **Product Summary**

BV <sub>DSS</sub>	Rds(on) max	I <sub>D MAX</sub> T <sub>A</sub> = +25°C
	52mΩ @ V <sub>GS</sub> = 10V	4A
30V	$65m\Omega @ V_{GS} = 4.5V$	3A
	$85m\Omega$ @ $V_{GS} = 2.5V$	2A

## **Applications**

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays

#### **Features**

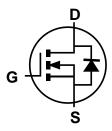
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

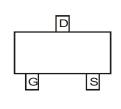






SOT23

Equivalent Circuit



Pin Configuration

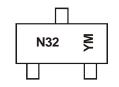
### **Ordering Information (Note 5)**

Part Number	Case	Packaging
DMG3402LQ-7	SOT23	3000/Tape & Reel
DMG3402LQ-13	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

#### Marking Information



 $\underbrace{N32}$  = Product Type Marking Code  $otag{\overline{Y}}$  M = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	20	021	2022	2023	3	2024	2025	202	26	2027
Code	G	Н		1	J	K		L	М	N		0
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

DMG3402LQ
Document number: DS41443 Rev. 2 - 2

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## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	±12	V
Drain Current (Note 6)	I <sub>D</sub>	4.0	А
Body-Diode Continuous Current (Note 6)	Is	1.5	A

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	$P_{D}$	1.4	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6)	$R_{\theta JA}$	90	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

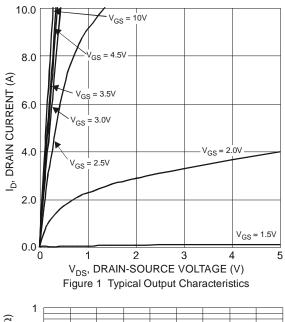
## Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

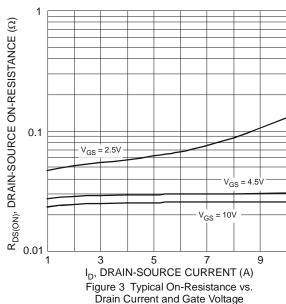
Characteristic	Symbol	Min	Tyro	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Syllibol	IVIIII	Тур	IVIAX	Onit	rest Condition	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS		_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Body Leakage	I <sub>GSS</sub>			±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	1655			±100	10.0	VGS - ±12V, VDS - 0V	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.6	_	1.4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			_	52		$V_{GS} = 10V, I_D = 4A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	_	65	mΩ	$V_{GS} = 4.5V, I_D = 3A$	
	,	_	_	85		$V_{GS} = 2.5V, I_D = 2A$	
Forward Transconductance	Y <sub>fs</sub>	_	6.6	_	S	$V_{DS} = 5V, I_{D} = 3.1A$	
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	_	_	1.16	V	$V_{GS} = 0V, I_{S} = 2.0A$	
DYNAMIC CHARACTERISTICS(Note 8)				•			
Gate Resistance	R <sub>g</sub>	_	2.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (10V)	Qg	_	11.7	_	nC	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 4 A	
Total Gate Charge (4.5V)	Qa	_	5.5	_	nC		
Gate-Source Charge	Qgs		1.1	_	nC	$V_{GS} = 10 \text{ V}, V_{DS} = 15 \text{ V},$	
Gate-Drain Charge	Q <sub>gd</sub>		1.8	_	nC	I <sub>D</sub> = 4 A	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	1.9	_	ns		
Turn-On Rise Time	t <sub>R</sub>		1.6	_	ns	$V_{DD} = 15V, V_{GEN} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	10.3	_	ns	$R_{GEN} = 3\Omega$ , $R_L = 3.75\Omega$	
Turn-Off Fall Time	t <sub>F</sub>		2.0	_	ns		
Input Capacitance	C <sub>iss</sub>	_	464	_	pF		
Output Capacitance	Coss		49.5	_	pF	$V_{DS} = 15V, V_{GS} = 0V$	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	43.8	_	pF	f = 1.0MHz	

Notes:

- 6. Device mounted on FR-4 PCB.  $t \le 5$  sec.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







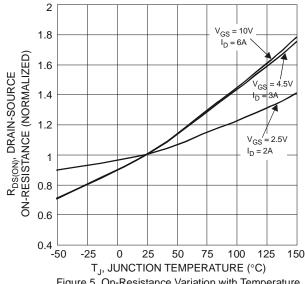
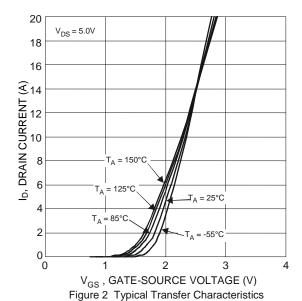
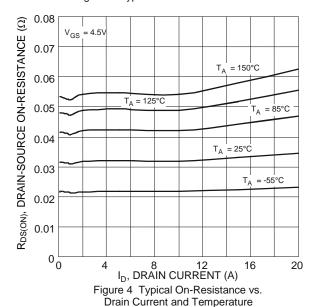
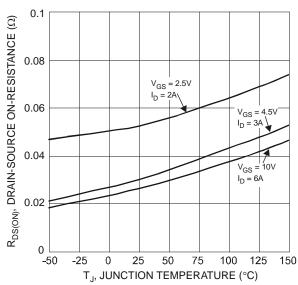


Figure 5 On-Resistance Variation with Temperature









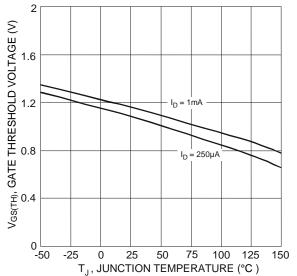
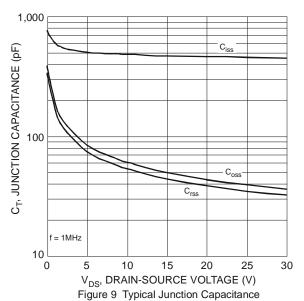
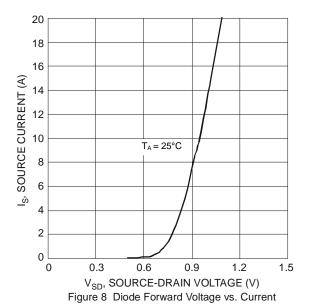
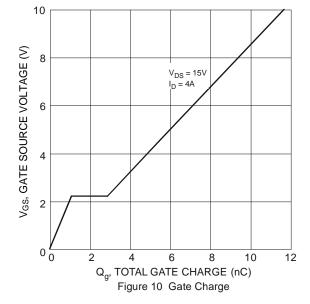


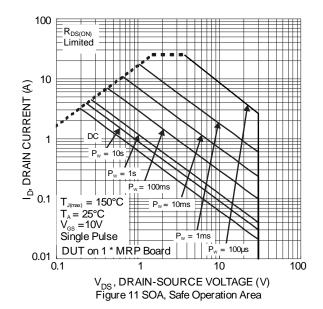
Figure 7 Gate Threshold Variation vs. Junction Temperature

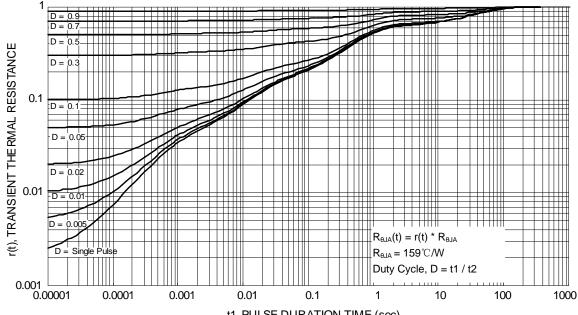










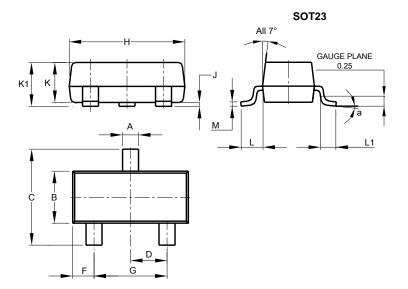


t1, PULSE DURATION TIME (sec) Figure 12 Transient Thermal Resistance



## **Package Outline Dimensions**

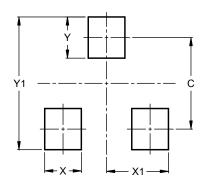
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



#### SOT23

Dimensions	Value (in mm)
C	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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